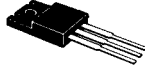


2SB1133



2041

PNP Triple Diffused Planar
Silicon Transistor

Low Frequency Power Amp Applications

(E)2419

Features

- . Wide ASO (adoption of MBIT process)
- . Micaless package facilitating mounting
- . High reliability

Absolute Maximum Ratings at Ta=25°C

			unit
Collector to Base Voltage	V _{CB0}	-60	V
Collector to Emitter Voltage	V _{CE0}	-60	V
Emitter to Base Voltage	V _{EBO}	-6	V
Collector Current	I _C	-3	A
Peak Collector Current	i _{cp}	-8	A
Collector Dissipation	P _C	2	W
		T _c =25°C	25
Junction Temperature	T _j	150	°C
Storage Temperature	T _{stg}	-55 to +150	°C

Electrical Characteristics at Ta=25°C

			min	typ	max	unit
Collector Cutoff Current	I _{CB0}	V _{CB} =-40V, I _E =0			-100	uA
Emitter Cutoff Current	I _{EBO}	V _{EB} =-4V, I _C =0			-100	uA
DC Current Gain	h _{FE} (1)	V _{CE} =-5V, I _C =-0.5A	70*		280*	
	h _{FE} (2)	V _{CE} =-5V, I _C =-3A	20			
Gain-Bandwidth Product	f _T	V _{CE} =-5V, I _C =-0.5A		40		MHz
Output Capacitance	c _{ob}	V _{CB} =-10V, f=1MHz		110		pF
C-E Saturation Voltage	V _{CE(sat)}	I _C =-2V, I _B =-0.2A	-0.6		-1	V
Base to Emitter Voltage	V _{BE}	V _{CE} =-5V, I _C =-0.5A	-0.7		-1	V
C-B Breakdown Voltage	V _{(BR)CBO}	I _C =-1mA, I _E =0	-60			V
C-E Breakdown Voltage	V _{(BR)CEO}	I _C =-5mA, R _{BE} =∞	-60			V
E-B Breakdown Voltage	V _{(BR)EBO}	I _E =-1mA, I _C =0	-6			V

*: The 2SB1133 is classified by 0.5A h_{FE} as follows:

70	Q	140	100	R	200	140	S	280
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Case Outline 2041 (unit:mm)

